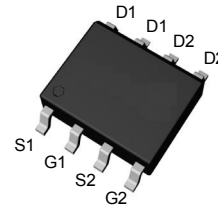


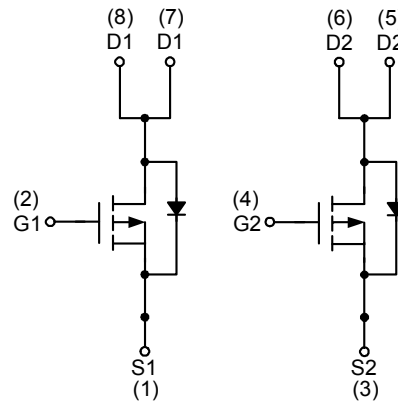
Features

- 30V/-12A,
 $R_{DS(ON)} = 12m\Omega(\text{max.}) @ V_{GS} = -10V$
 $R_{DS(ON)} = 18m\Omega(\text{max.}) @ V_{GS} = -4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Pin Description



Top View of SOP-8



P-Channel MOSFET

Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit	
Common Ratings				
V_{DSS}	Drain-Source Voltage	-30	V	
V_{GSS}	Gate-Source Voltage	± 20		
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150		
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	-12	A
		$T_A = 70^\circ\text{C}$	- 8	
I_{DM}^a	Pulsed Drain Current	$T_A = 25^\circ\text{C}$	-35	
P_D	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	2.5	W
		$T_A = 70^\circ\text{C}$	1.6	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	$t \leq 10s$	50	$^\circ\text{C/W}$
		Steady State	90	
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	Steady State	20	
I_{AS}^b	Avalanche Current, Single pulse	$L = 0.1mH$	24	A
		$L = 0.5mH$	14	
E_{AS}^b	Avalanche Energy, Single pulse	$L = 0.1mH$	29	mJ
		$L = 0.5mH$	49	

Note a Pulse width is limited by maximum junction temperature.

Note b UIS tested and pulse width are limited by maximum junction temperature 150°C (initial temperature $T_i = 25^\circ\text{C}$).